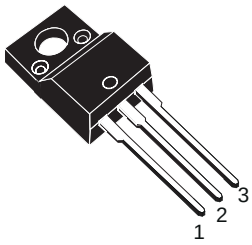
BDW93CFP
BDW94CFP

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- MONOLITHIC DARLINGTON CONFIGURATION
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE
- FULLY MOLDED INSULATED PACKAGE
- 2000 V DC INSULATION (U.L. COMPLIANT)



T0-220FP

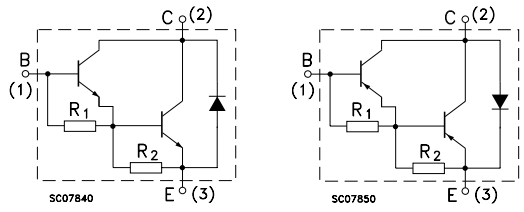
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The BDW93CFP is a silicon Epitaxial-Base NPN transistor in monolithic Darlington configuration mounted in TO-220FP fully molded insulated package. It is intented for use in power linear and switching applications.
The complementary PNP type is the BDW94CFP.

INTERNAL SCHEMATIC DIAGRAM



R_1 Typ. = 10 KΩ R_2 Typ. = 150 Ω

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		NPN	BDW93CFP	
		PNP	BDW94CFP	
V_{CBO}	Collector-Base Voltage (I_E = 0)		100	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)		100	V
I_C	Collector Current		12	A
I_{CM}	Collector Peak Current		15	A
I_B	Base Current		0.2	A
P_{tot}	Total Dissipation at $T_c \leq 25\ ^oC$		33	W
T_{stg}	Storage Temperature		-65 to 150	^oC
T_j	Max. Operating Junction Temperature		150	^oC

For PNP types voltage and current values are negative.

THERMAL DATA

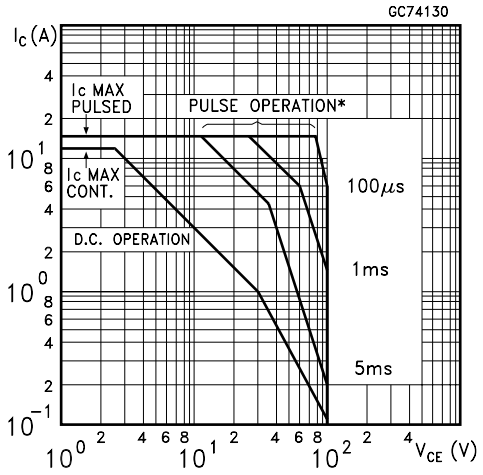
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	3.8	$^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = 100 V V_{CB} = 100 V T_{case} = 150 ^oC			100 5	µA mA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{CE} = 80 V			1	mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 5 V			2	mA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage (I_B = 0)	I_C = 100 mA	100			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 5 A I_B = 20 mA I_C = 10 A I_B = 100 mA			2 3	V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 5 A I_B = 20 mA I_C = 10 A I_B = 100 mA			2.5 4	V V
h_{FE}*	DC Current Gain	I_C = 3 A V_{CE} = 3 V I_C = 5 A V_{CE} = 3 V I_C = 10 A V_{CE} = 3 V	1000 750 100		 20000	
V_F*	Parallel-diode Forward Voltage	I_F = 5 A I_F = 10 A		1.3 1.8	2 4	V V
h_{fe}	Small Signal Current Gain	I_C = 1 A V_{CE} = 10 V f = 1 MHz	20			

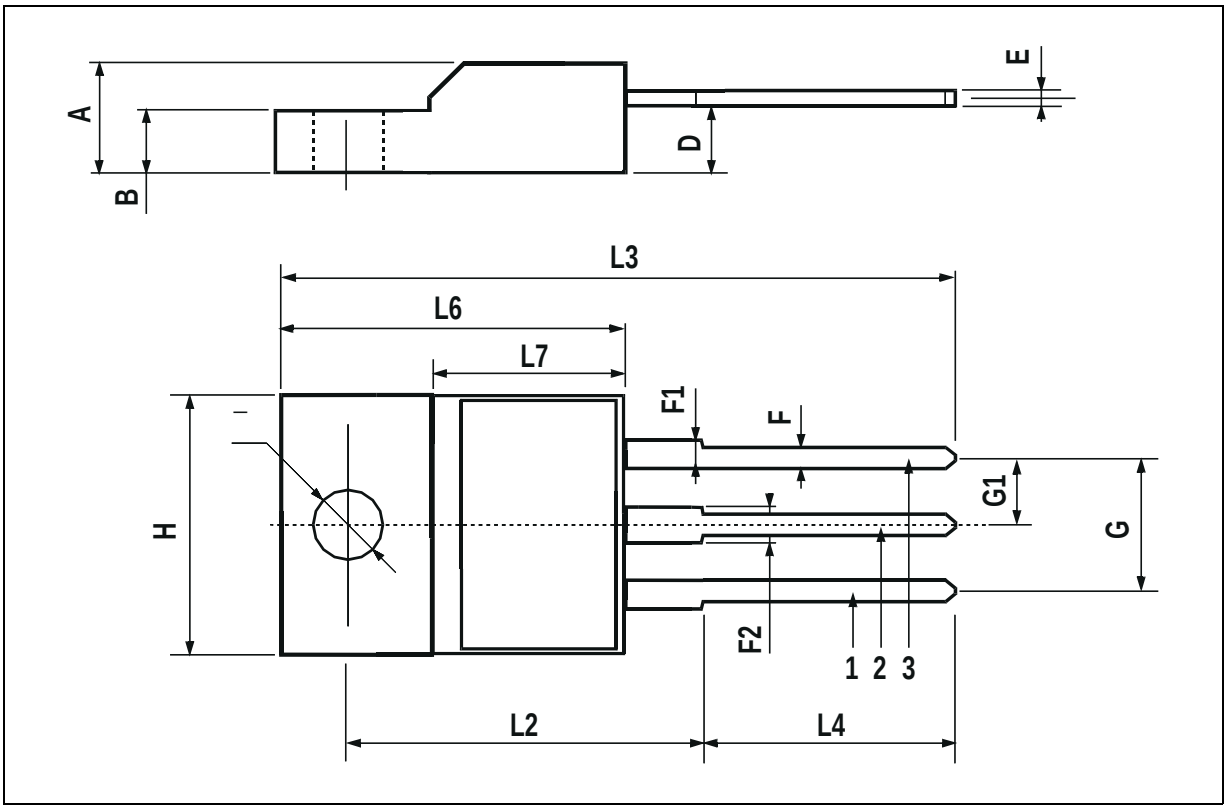
* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

Safe Operating Area



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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